

No.4500

2SK1848

N-Channel MOS Silicon FET
Very High-Speed
Switching Applications

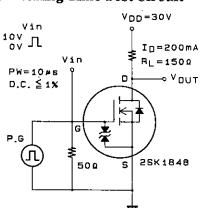
Features

- · Low ON resistance.
- · Very high-speed switching.
- · Low-voltage drive.

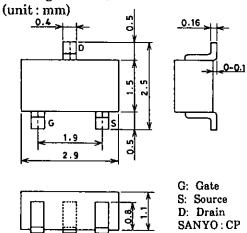
Absolute Maximum Ratings at Ta = 25°C					unit	
Drain to Source Voltage	$V_{\rm DSS}$			60	V	
Gate to Source Voltage	V_{GSS}		3	£ 15	V	
Drain Current(DC)	$I_{\mathbf{D}}$			400	mΑ	
Drain Current(Pulse)	I_{DP}	$PW \le 10 \mu s$, duty cycle $\le 1\%$		1.6	Α	
Allowable Power Dissipation	P_{D}			250	mW	
Channel Temperature	Tch	-		150	°C	
Storage Temperature	Tstg		-55 to $+$		°Č	
Electrical Characteristics at Ta = 25°C			min	typ	max	unit
D-S Breakdown Voltage		$I_D = 1 \text{ mA, } V_{GS} = 0$	60	₹J P		v
Zero Gate Voltage	IDSS	$V_{DS} = 60 V_1 V_{GS} = 0$			10	$\mu { m A}$
Drain Current	200	<i>DD</i> ,				,
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0$			±10	μ A
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10V, I_D = 1mA$	1.0		2.0	v
Forward Transfer Admittance	y _{fs}	$V_{DS} = 10V, I_D = 200 \text{mA}$	300	600		mS
Static Drain to Source	$R_{DS(on)}$	$I_D = 200 \text{mA}, V_{GS} = 10 \text{V}$		0.9	1.2	Ω
on State Resistance	R _{DS(on)}	$I_D = 200 \text{ mA}, V_{GS} = 4 \text{ V}$		1.2	1.6	Ω
Input Capacitance	Ciss	$V_{DS} = 20V, f = 1MHz$		45	_, -, -	рF
Output Capacitance	Coss	$V_{DS} = 20V, f = 1MHz$		22		рF
Reverse Transfer Capacitance	Crss	$V_{DS} = 20V, f = 1MHz$		5		рF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		5		ns
Rise Time	$\mathbf{t_r}$	4		10		ns
Turn-OFF Delay Time	t _{d(off)}	"		35		ns
Fall Time	t _f	"		25		ns
Diode Forward Voltage	v_{sd}	$I_S = 400 \text{mA}, V_{GS} = 0$		0.9		v

Marking: LJ

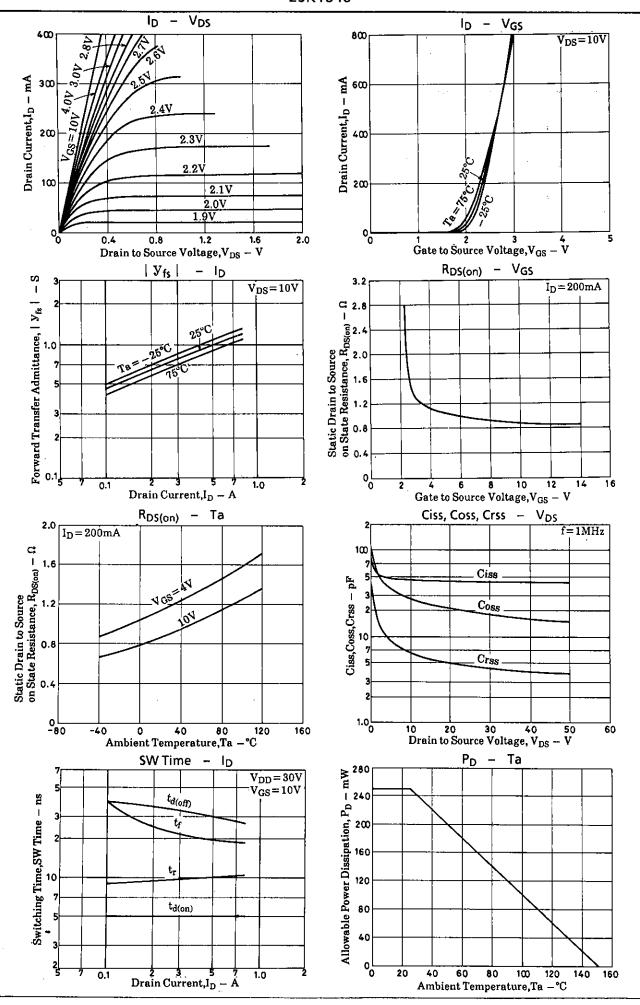
Switching Time Test Circuit



Package Dimensions 2091



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